Low Noise Transistors NPN Silicon

BC549B,C BC550B,C

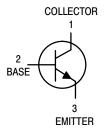
MAXIMUM RATINGS

Rating	Symbol	BC549	BC550	Unit
Collector–Emitter Voltage	V _{CEO}	30	45	Vdc
Collector-Base Voltage	V _{CBO}	30	50	Vdc
Emitter-Base Voltage	V _{EBO}	5.0		Vdc
Collector Current — Continuous	I _C	100		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0		mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W



$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

Characterist	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	BC549B,C BC550B,C	V _{(BR)CEO}	30 45			Vdc	
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	BC549B,C BC550B,C	V _(BR) CBO	30 50			Vdc	
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	5.0	_	_	Vdc	
Collector Cutoff Current $(V_{CB} = 30 \text{ V}, I_E = 0)$ $(V_{CB} = 30 \text{ V}, I_E = 0, T_A = +125^{\circ}\text{C})$		I _{CBO}	_		15 5.0	nAdc μAdc	
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)		I _{EBO}	_	_	15	nAdc	

BC549B,C BC550B,C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit	
ON CHARACTERISTICS							
DC Current Gain ($I_C = 10 \mu Adc, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	BC549B/550B BC549C/550C BC549B/550B BC549C/550C	h _{FE}	100 100 200 420	150 270 290 500	— — 450 800	_	
Collector–Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0.5 \text{ mAdc}$) ($I_C = 10 \text{ mAdc}$, $I_B = \text{see note 1}$) ($I_C = 100 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$, see note 2)		V _{CE(sat)}	_ _ _	0.075 0.3 0.25	0.25 0.6 0.6	Vdc	
Base–Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 5.0 mAdc)		V _{BE(sat)}	_	1.1	_	Vdc	
Base–Emitter On Voltage (I_C = 10 μ Adc, V_{CE} = 5.0 Vdc) (I_C = 100 μ Adc, V_{CE} = 5.0 Vdc) (I_C = 2.0 mAdc, V_{CE} = 5.0 Vdc)		V _{BE(on)}	— — 0.55	0.52 0.55 0.62	_ _ 0.7	Vdc	
SMALL-SIGNAL CHARACTERISTICS							
Current–Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	_	250	_	MHz	
Collector–Base Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{cbo}	_	2.5	_	pF	
Small–Signal Current Gain ($I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC549B/BC550B BC549C/BC550C	h _{fe}	240 450	330 600	500 900	_	
Noise Figure $ \begin{aligned} &\text{(I}_{C} = 200 \; \mu\text{Adc, V}_{CE} = 5.0 \; \text{Vdc, R}_{S} = 2.0 \; \text{k}\Omega, \\ &\text{(I}_{C} = 200 \; \mu\text{Adc, V}_{CE} = 5.0 \; \text{Vdc, R}_{S} = 100 \; \text{k}\Omega, \end{aligned} $		NF ₁ NF ₂	_	0.6 —	2.5 10	dB	

NOTES:

- 1. I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V. 2. Pulse test = 300 μ s Duty cycle = 2%.

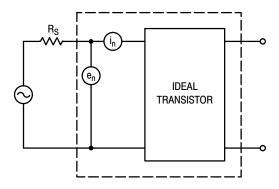


Figure 1. Transistor Noise Model

BC549B,C BC550B,C

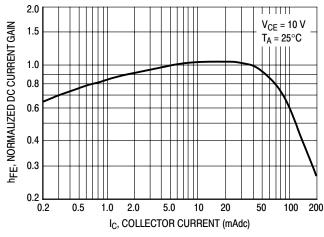


Figure 2. Normalized DC Current Gain

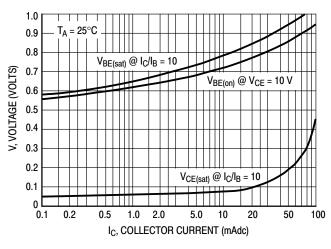


Figure 3. "Saturation" and "On" Voltages

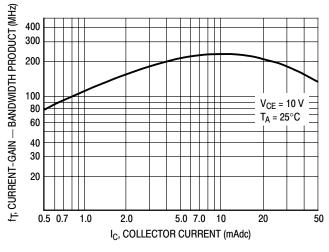


Figure 4. Current-Gain — Bandwidth Product

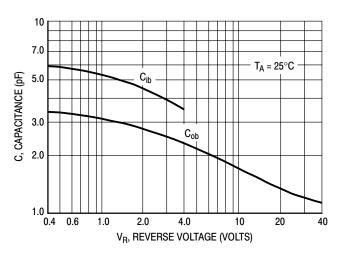


Figure 5. Capacitance

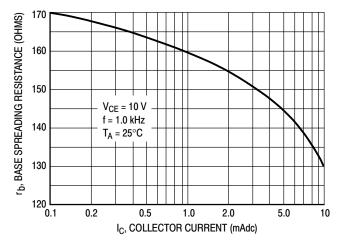
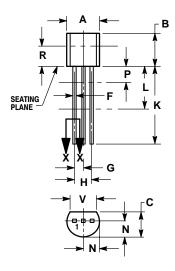


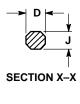
Figure 6. Base Spreading Resistance

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PACKAGE DIMENSIONS

CASE 029-04 (TO-226AA) ISSUE AD





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 17:

PIN 1. COLLECTOR 2. BASE EMITTER

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